



#### **GP2M002A065HG Information**



For Reference Only

Part Number GP2M002A065HG

ManufacturerGlobal Power Technologies GroupCategoryDiscrete Semiconductor Products<br/>Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 650V 1.8A TO220

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **GP2M002A065HG Specifications**

Manufacturer Part Number         GP2M002A065HG           Manufacturer         Global Power Technologies Group           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         1.8A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         8.5nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         353pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         52W (Tc)           Rds On (Max) @ Id, Vgs         4.6 Ohm @ 900mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220           Package / Case         TO-220-3		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         650V           Current - Continuous Drain (Id) @ 25°C         1.8A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         5V @ 250µA           Gate Charge (Qg) (Max) @ Vgs         8.5nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         353pF @ 25V           Vgs (Max)         ±30V           FET Feature         -           Power Dissipation (Max)         52W (Tc)           Rds On (Max) @ Id, Vgs         4.6 Ohm @ 900mA, 10V           Operating Temperature         -55°C ~ 150°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220           Package / Case         TO-220-3	Manufacturer Part Number	GP2M002A065HG
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FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)650VCurrent - Continuous Drain (Id) @ 25°C1.8A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs8.5nC @ 10VInput Capacitance (Ciss) (Max) @ Vds353pF @ 25VVgs (Max)±30VFET Feature-Power Dissipation (Max)52W (Tc)Rds On (Max) @ Id, Vgs4.6 Ohm @ 900mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220Package / CaseTO-220-3	Package	TO-220-3
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Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  As On (Max) @ Id, Vgs  Operating Temperature  Supplier Device Package  Package / Case  Sys (Max)  Sys (Max)  Sys (Max)  FET Feature  -  To-220-3	Current - Continuous Drain (Id) @ 25°C	1.8A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  Jemperature  Through Hole  Supplier Device Package  TO-220  Package / Case  8.5nC @ 10V  900mA, 10V  10V  10Figure 10F	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  7 Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.6 Ohm @ 900mA, 10V  Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220  Package / Case  TO-220-3	Vgs(th) (Max) @ Id	5V @ 250μA
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Operating Temperature  -55°C ~ 150°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220  Package / Case  TO-220-3	Power Dissipation (Max)	52W (Tc)
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Supplier Device Package TO-220 Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220
Report errors?	Package / Case	TO-220-3
		Report errors?

#### GP2M002A065HG Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **GP2M002A065HG Payment Methods**



















### **GP2M002A065HG Shipping Methods**













If you have any question about GP2M002A065HG, please do not hesitate to contact us!

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